

# **CORNERSTONE STANDARD COMPONENTS LIBRARY**

(On SOI Platforms)



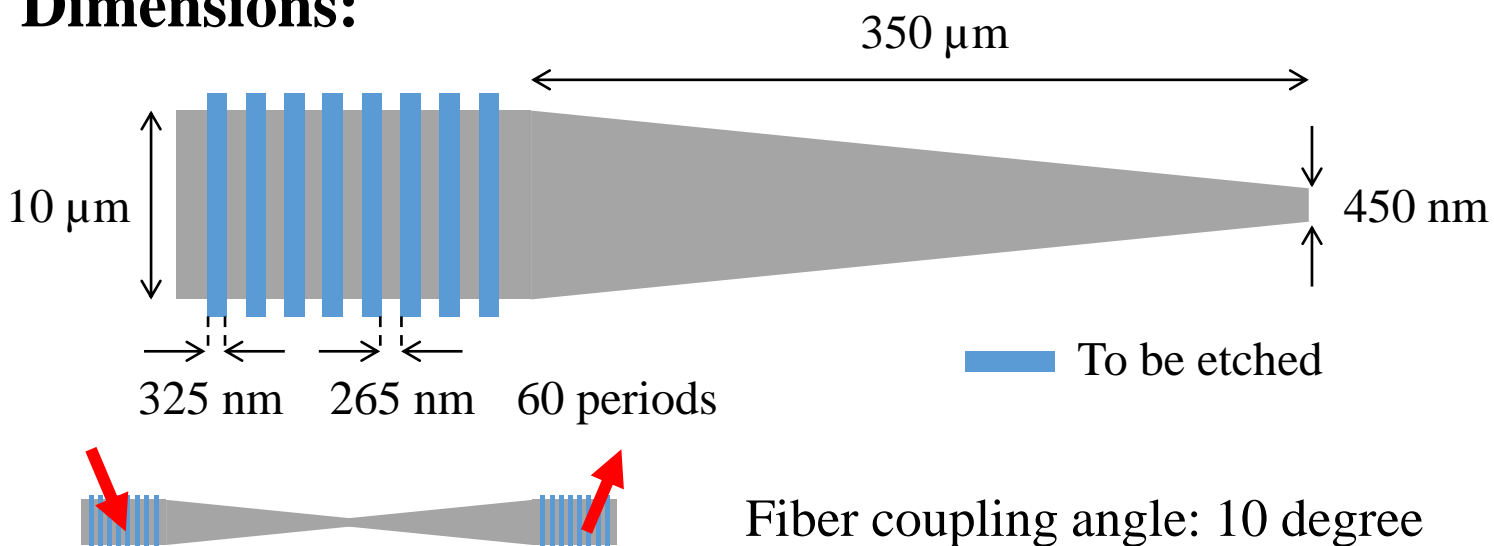


- **Wavelength: 1550 nm**
- **Platform: 340 nm SOI**

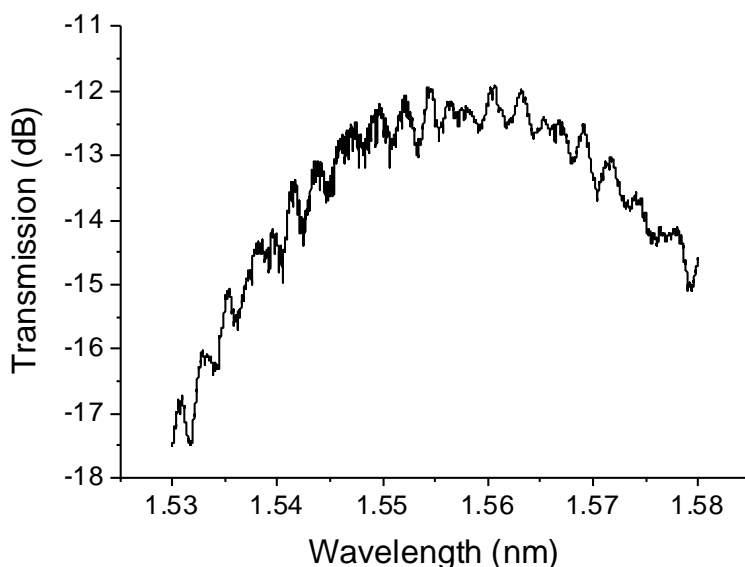
# SOI340nm\_1550nm\_TE\_STRIP\_Grating\_Coupler

<b>Platform:</b>	340 nm SOI (2 um BOX layer)
<b>Wavelength:</b>	1550 nm
<b>Etching depth:</b>	140 nm (Grating etch depth)
<b>Polarization:</b>	TE
<b>Cell name in GDS lib:</b>	SOI340nm_1550nm_TE_STRIP_Grating_Coupler

## Dimensions:



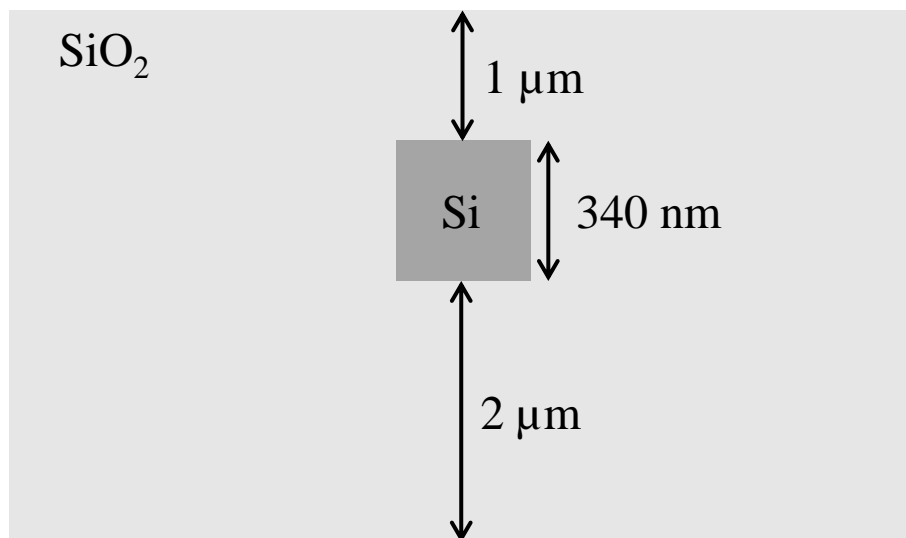
## Measured transmission spectrum



## Summarized performance:

- Coupling efficiency: 5-7 dB
- 1 dB bandwidth: > 35 nm
- Center wavelength: 1550-1570 nm

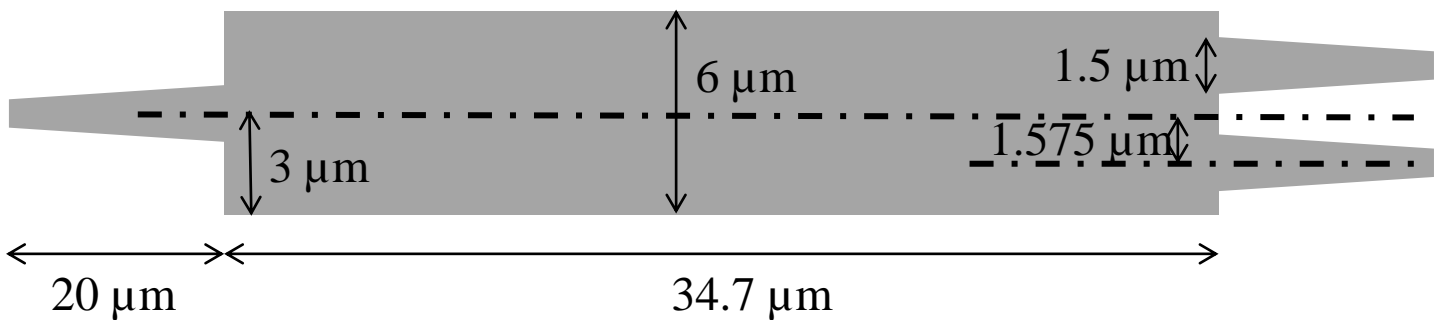
- Wavelength: 1550 nm
- Platform: 340 nm SOI
- **STRIP**



## SOI340nm\_1550nm\_TE\_STRIP\_2x1\_MMI

<b>Platform:</b>	340 nm SOI (2 um BOX layer)
<b>Wavelength:</b>	1550 nm
<b>Etching depth:</b>	340 nm (Strip design)
<b>Polarization:</b>	TE
<b>Cell name in GDS lib:</b>	SOI340nm_1550nm_TE_STRIP_2x1_MMI

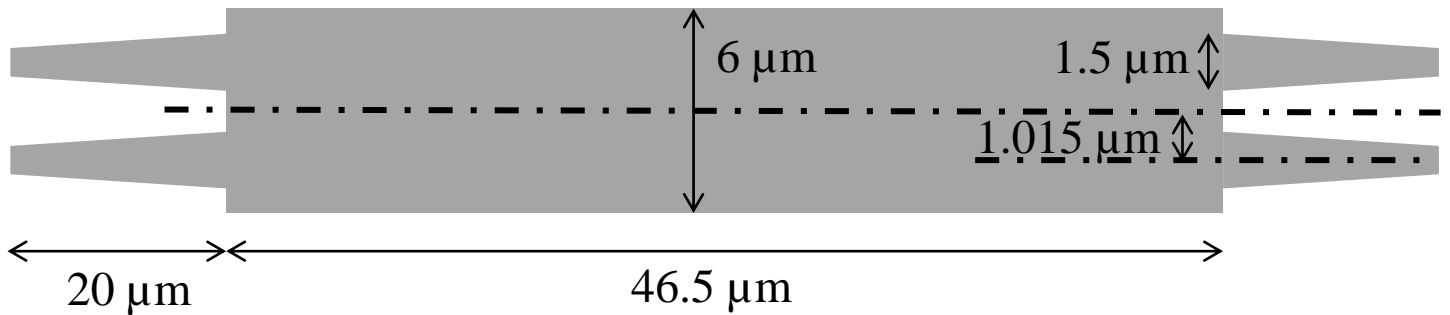
### Dimensions:



## SOI340nm\_1550nm\_TE\_STRIP\_2x2\_MMI

<b>Platform:</b>	340 nm SOI (2 um BOX layer)
<b>Wavelength:</b>	1550 nm
<b>Etching depth:</b>	340 nm (Strip design)
<b>Polarization:</b>	TE
<b>Cell name in GDS lib:</b>	SOI340nm_1550nm_TE_STRIP_2x2_MMI

### Dimensions:



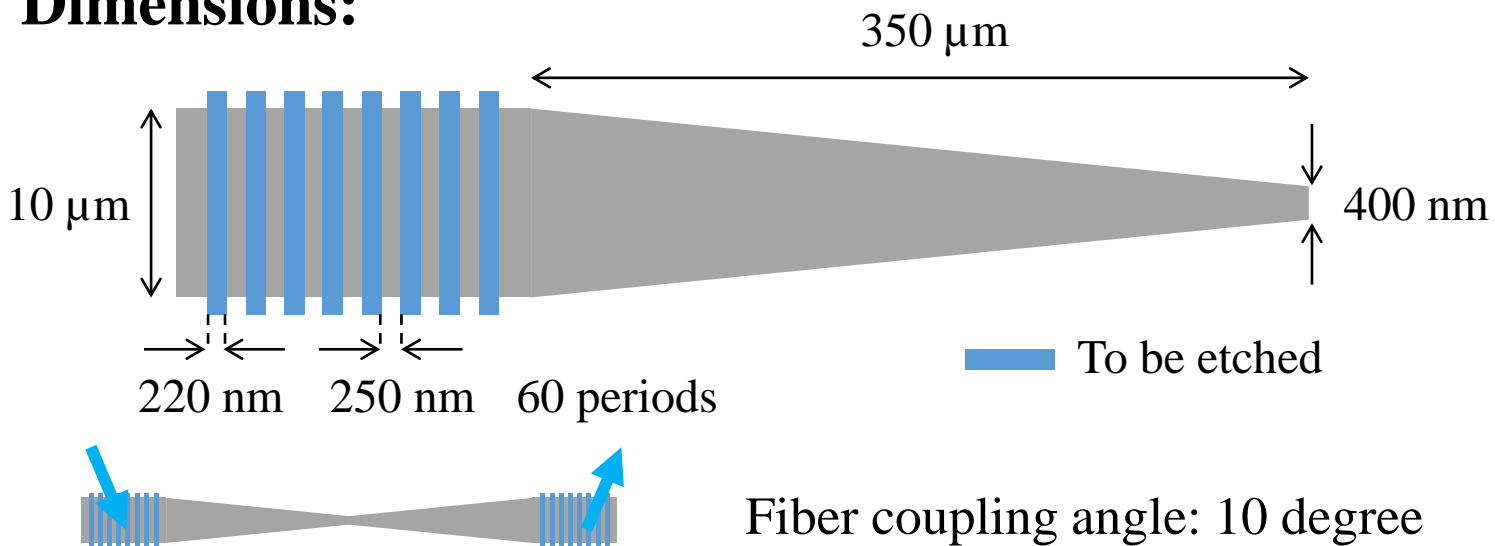


- **Wavelength: 1310 nm**
- **Platform: 340 nm SOI**

# SOI340nm\_1310nm\_TE\_STRIP\_Grating\_Coupler

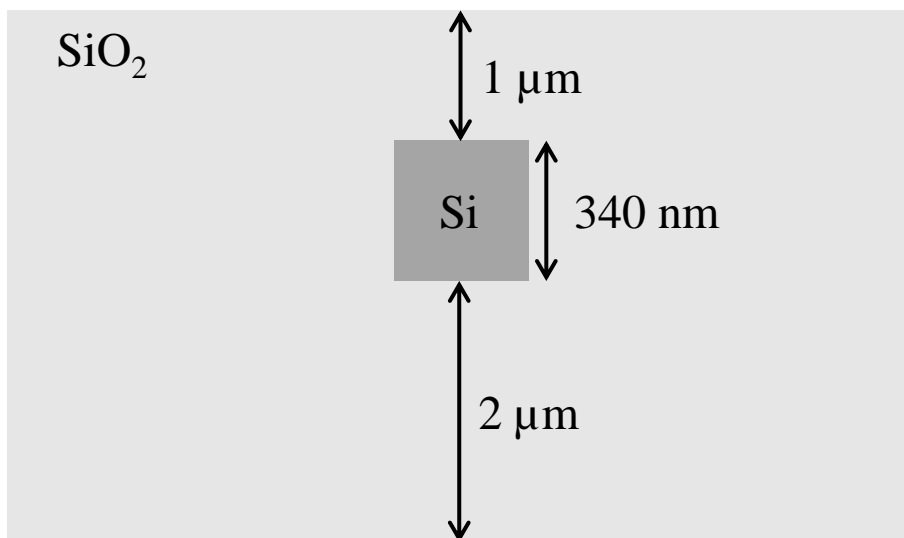
<b>Platform:</b>	340 nm SOI (2 um BOX layer)
<b>Wavelength:</b>	1310 nm
<b>Etching depth:</b>	140 nm (Grating etch depth)
<b>Polarization:</b>	TE
<b>Cell name in GDS lib:</b>	SOI340nm_1310nm_TE_STRIP_Grating_Coupler

## Dimensions:





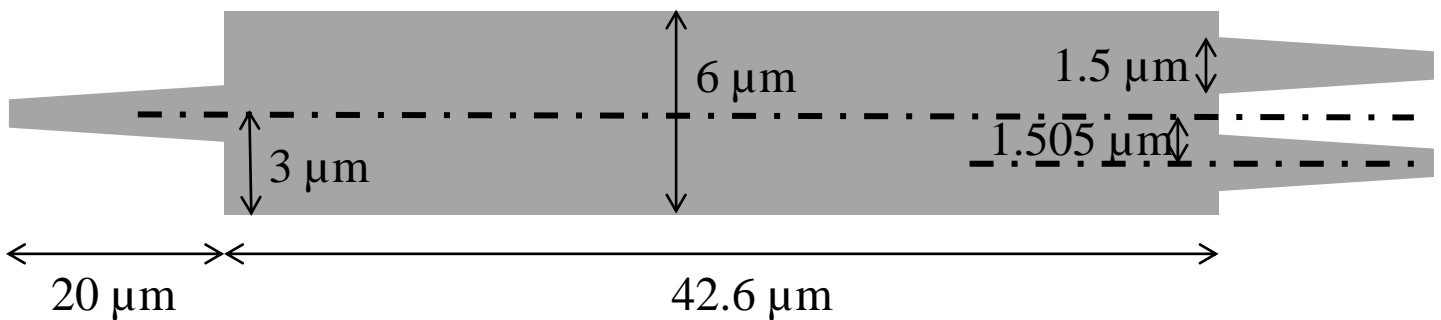
- Wavelength: 1310 nm
- Platform: 340 nm SOI
- **STRIP**



## SOI340nm\_1310nm\_TE\_STRIP\_2x1\_MMI

<b>Platform:</b>	340 nm SOI (2 um BOX layer)
<b>Wavelength:</b>	1310 nm
<b>Etching depth:</b>	340 nm (Strip design)
<b>Polarization:</b>	TE
<b>Cell name in GDS lib:</b>	SOI340nm_1310nm_TE_STRIP_2x1_MMI

### Dimensions:



# SOI340nm\_1310nm\_TE\_STRIP\_2x2\_MMI

<b>Platform:</b>	340 nm SOI (2 um BOX layer)
<b>Wavelength:</b>	1310 nm
<b>Etching depth:</b>	340 nm (Strip design)
<b>Polarization:</b>	TE
<b>Cell name in GDS lib:</b>	SOI340nm_1310nm_TE_STRIP_2x2_MMI

## Dimensions:

